

2SA984
984K
2SC2274
2274K



2003A

PNP/NPN Epitaxial Planar
Silicon Transistors

T-29-21

Low-Frequency Power Amp Applications

©465F

Features

- High breakdown voltage ($V_{CE0} \geq 50/80V$).
- High current ($I_C = 500mA$).
- Low saturation voltage.

(): 2SA984, 984K

Absolute Maximum Ratings at Ta=25°C		A984, C2274	A984K, C2274K	unit
Collector to Base Voltage	V _{CB0}	(-)60	(-)100	V
Collector to Emitter Voltage	V _{CE0}	(-)50	(-)80	V
Emitter to Base Voltage	V _{EB0}		(-)5	V
Collector Current	I _C		(-)500	mA
Peak Collector Current	i _{cp}		(-)800	mA
Collector Dissipation	P _C		600	mW
Junction Temperature	T _j		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

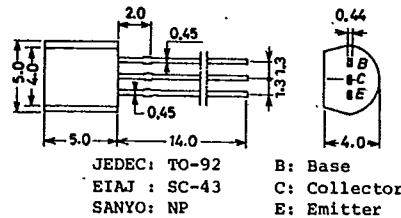
Electrical characteristics at Ta=25°C

		min	typ	max	unit
Collector Cutoff Current	I _{CB0} V _{CB} =(-)40V, I _E =0			(-)1.0	uA
Emitter Cutoff Current	I _{EB0} V _{EB} =(-)4V, I _C =0			(-)1.0	uA
DC Current Gain	h _{FE} (1) V _{CE} =(-)5V, I _C =(-)50mA		60*	320*	
	h _{FE} (2) V _{CE} =(-)5V, I _C =(-)400mA (pulse)		35		
Gain-Bandwidth Product	f _T V _{CE} =(-)10V, I _C =(-)10mA		120		MHz
Output Capacitance	c _{ob} V _{CB} =(-)10V, f=1MHz		(9)		pF
			5		pF
C-E Saturation Voltage	V _{CE} (sat) (I _C =(-)400mA, I _B =(-)40mA)			(-0.25) (-0.6)	V
B-E Saturation Voltage	V _{BE} (sat) " "			0.2 0.6	V
C-B Breakdown Voltage	V(BR)CBO (I _C =(-)10uA, I _E =0)			(-)60	V
				A984K, C2274K (-)100	V
C-E Breakdown Voltage	V(BR)CEO (I _C =(-)1mA, R _{BE} =∞)			(-)50	V
				A984K, C2274K (-)80	V
E-B Breakdown Voltage	V(BR)EBO (I _E =(-)10uA, I _C =0)			(-)5	V

* The 2SA984, K, 2SC2274, K are classified by 50mA h_{FE} as follows.

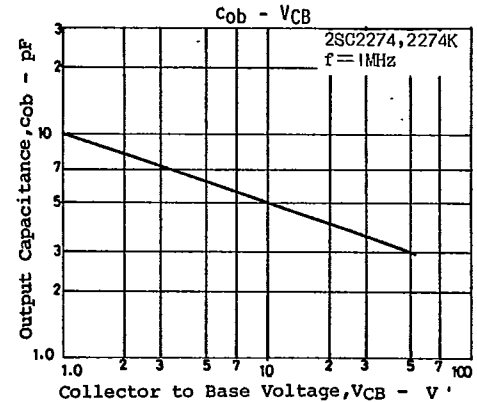
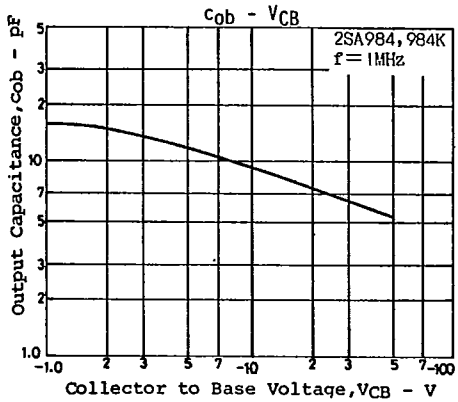
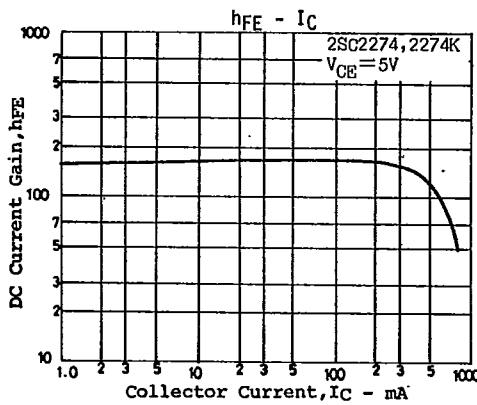
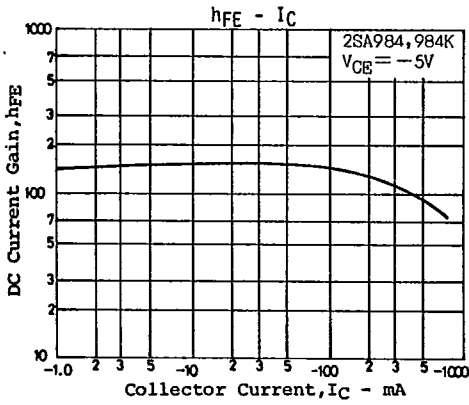
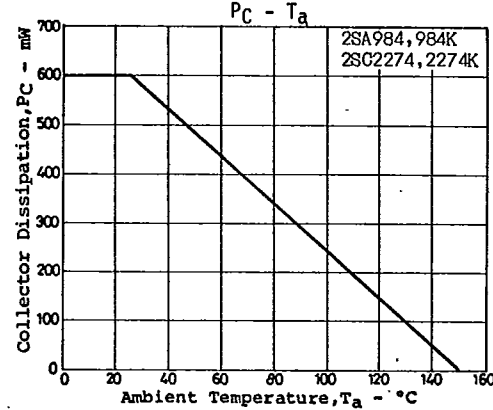
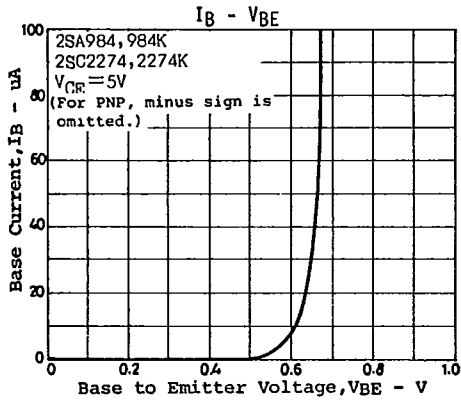
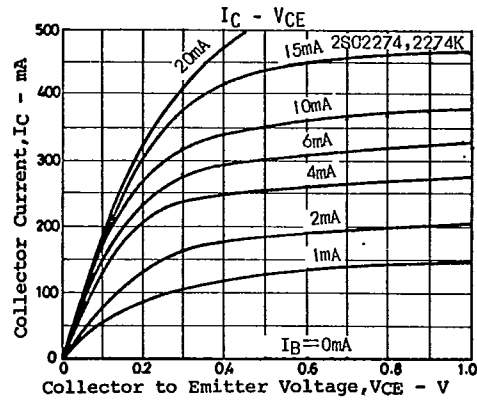
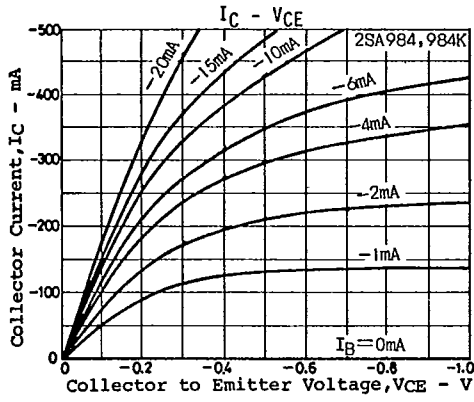
60	D	120	100	E	200	160	F	320
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Case Outline 2003A (unit:mm)



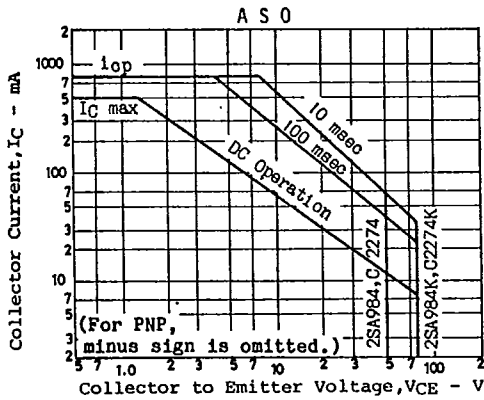
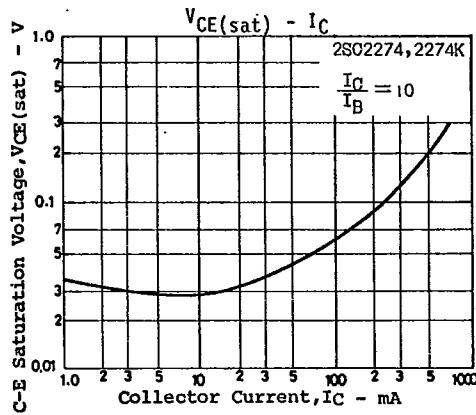
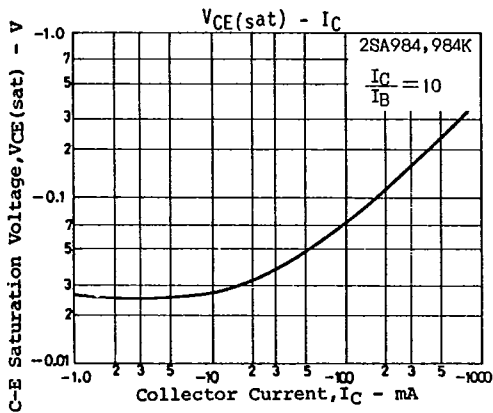
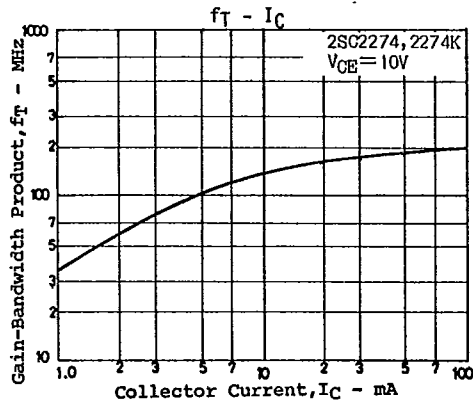
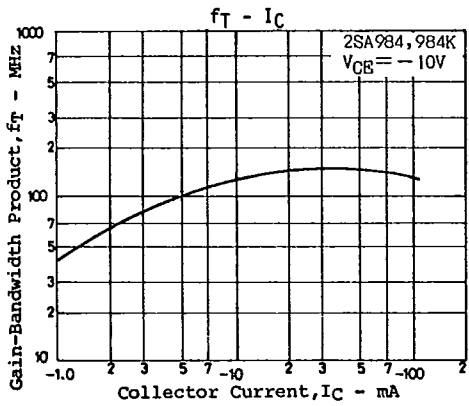
The 2SC2274K is scheduled to be discontinued soon. Use the 2SC3708, instead of the 2SC2274K, in new applications where you are planning to use the 2SC2274K.

3187AT/3155MY, TS No. 465-1/3



2SA984,984K/2SC2274,2274K

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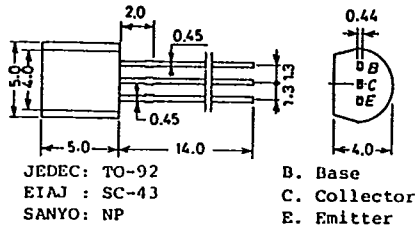


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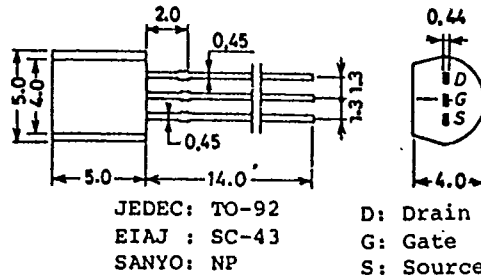
CASE OUTLINES OF LEAD FORMED SMALL SIGNAL TRANSISTORS

- All of Sanyo lead formed small signal transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.

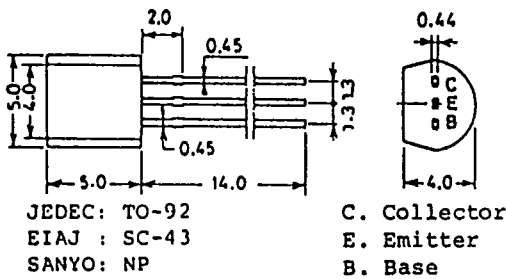
Case Outline-[2003A] unit: mm



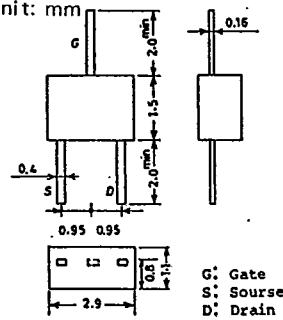
Case Outline-[2019A] unit: mm



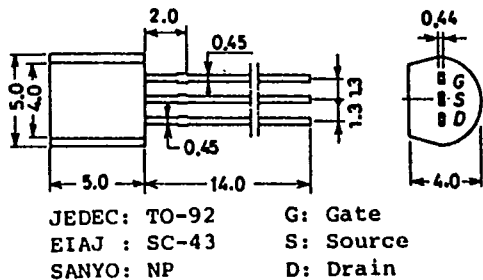
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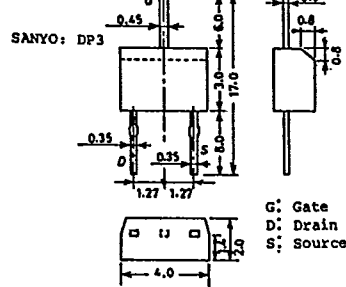
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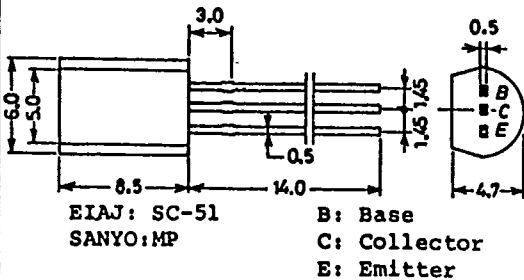
Case Outline-[2005A] unit: mm



Case Outline-[2026] unit: mm



Case Outline-[2006A] unit: mm



Case Outline-[2027A] unit: mm

